

Abstract of the Disclosure

In bit line cladding structure formation, stability and margin of the process are secured and further shrinking is achieved, and the magnetic memory device is improved in speed, reliability and yield. Method for manufacturing a magnetic memory device, comprising the steps of: forming a word line; forming a magnetoresistance effect memory element comprising a tunnel insulating layer disposed between a ferromagnetic material and being electrically insulated from the word line; forming an insulating film for covering the memory element; and forming a bit line so that it is buried in the insulating film wherein the bit line is electrically connected to the memory element and spatially crosses the word line through the memory element disposed therebetween, wherein the method has steps of removing the insulating film on the bit line side to expose the bit line and forming a soft magnetic material layer selectively only on the bit line surface.